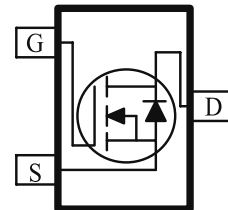
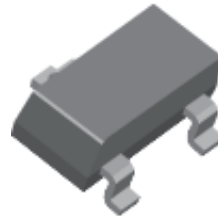


N-Channel 20V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipating. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
20	0.058 @ $V_{GS} = 4.5$ V	2.0
	0.082 @ $V_{GS} = 2.5$ V	1.7

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SC70-3 saves board space
- Fast switching speed
- High performance trench technology



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 8	
Continuous Drain Current ^a	$T_A = 25^\circ\text{C}$	I_D	2.0	A
	$T_A = 70^\circ\text{C}$		1.7	
Pulsed Drain Current ^b		I_{DM}	± 20	
Continuous Source Current (Diode Conduction) ^a		I_S	1.6	A
Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	0.34	W
	$T_A = 70^\circ\text{C}$		0.22	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{THJA}	100	$^\circ\text{C/W}$
	Steady-State		166	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 uA	0.7			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V			1	uA
		V _{DS} = 16 V, V _{GS} = 0 V, T _J = 55°C			10	
On-State Drain Current ^A	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 4.5 V	10			A
Drain-Source On-Resistance ^A	r _{DS(on)}	V _{GS} = 4.5 V, I _D = 2.0 A			58	mΩ
		V _{GS} = 2.5 V, I _D = 1.7 A			82	
Forward Tranconductance ^A	g _{fs}	V _{DS} = 10 V, I _D = 2.0 A		11.3		S
Diode Forward Voltage	V _{SD}	I _S = 1.6 A, V _{GS} = 0 V		0.75		V
Dynamic ^b						
Total Gate Charge	Q _g	V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 2.0 A		7.5		nC
Gate-Source Charge	Q _{gs}			0.6		
Gate-Drain Charge	Q _{gd}			1.0		
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1MHz		720		pF
Output Capacitance	C _{oss}			165		
Reverse Transfer Capacitance	C _{rss}			60		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 15 Ω, I _D = 1 A, V _{GEN} = 4.5 V		8		ns
Rise Time	t _r			24		
Turn-Off Delay Time	t _{d(off)}			35		
Fall-Time	t _f			10		

Notes

- Pulse test: PW ≤ 300us duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

Typical Electrical Characteristics (N-Channel)

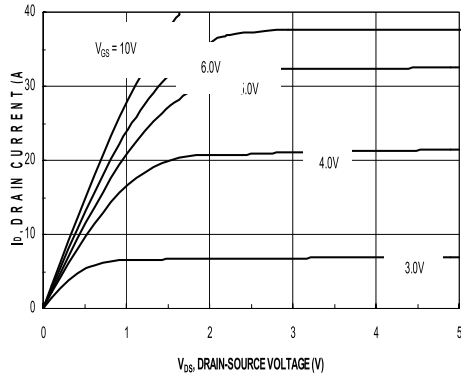


Figure 1. On-Region Characteristics

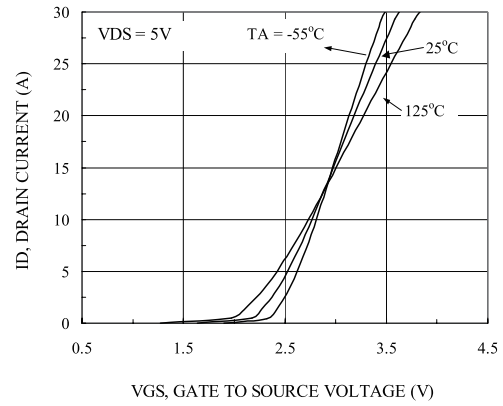


Figure 2. Body Diode Forward Voltage Variation with Source Current and Temperature

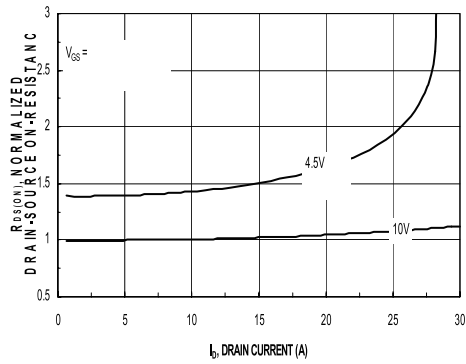


Figure 3. On Resistance Vs V_{GS} Voltage

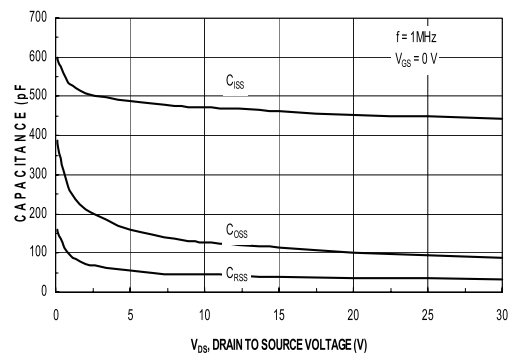


Figure 4. Capacitance Characteristics

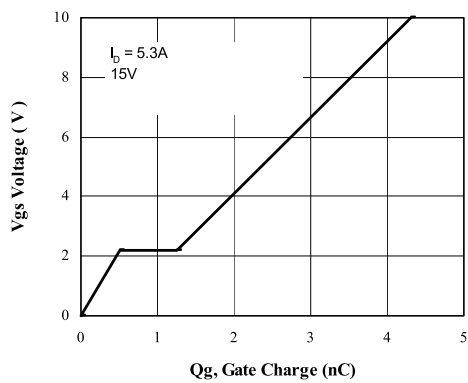


Figure 5. Gate Charge Characteristics

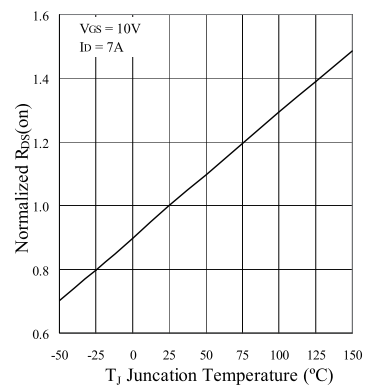


Figure 6. On-Resistance Variation with Temperature

Typical Electrical Characteristics (N-Channel)

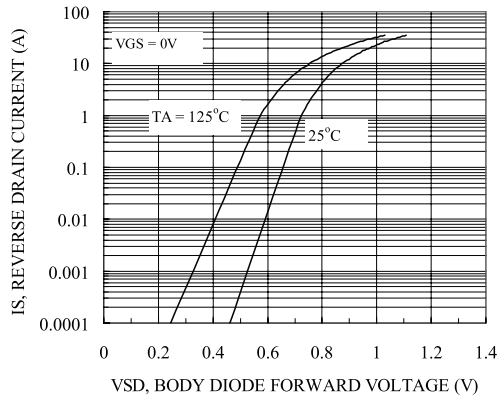


Figure 7. Transfer Characteristics

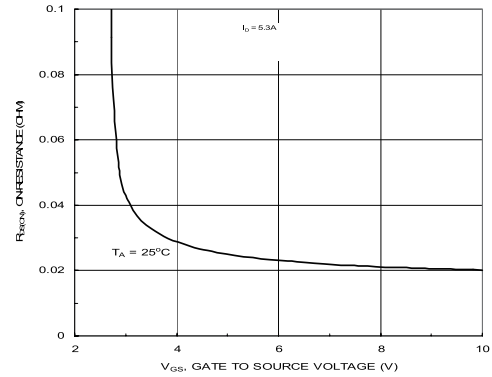


Figure 8. On-Resistance with Gate to Source Voltage

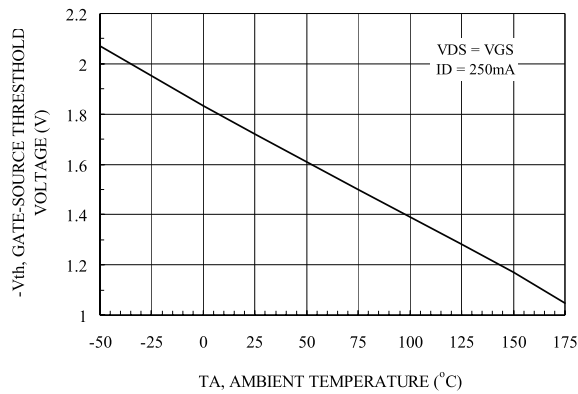


Figure 9. Vth Gate to Source Voltage Vs Temperature

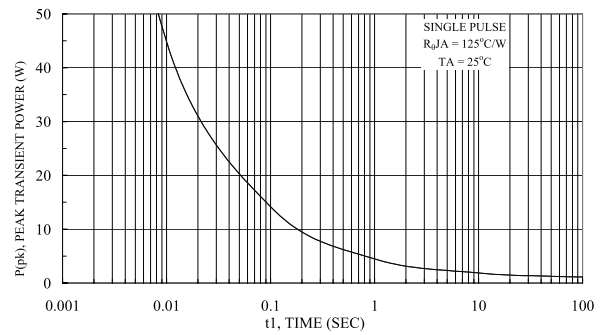


Figure 10. Single Pulse Maximum Power Dissipation

Normalized Thermal Transient Junction to Ambient

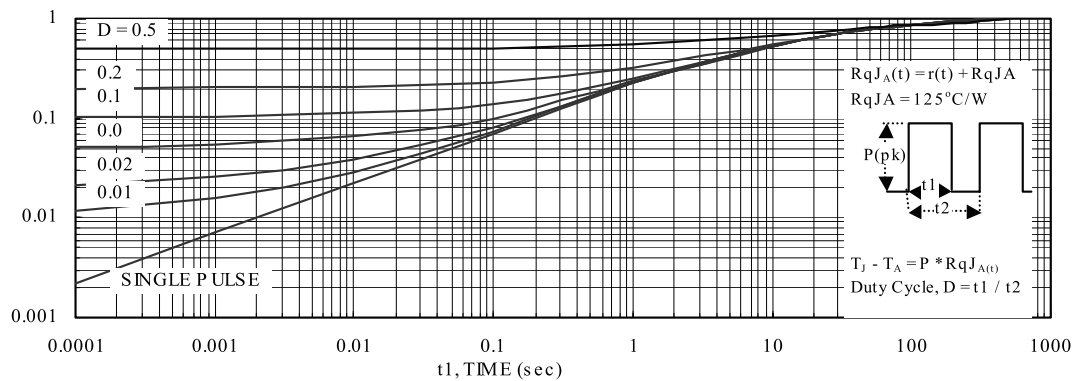


Figure 11. Transient Thermal Response Curve